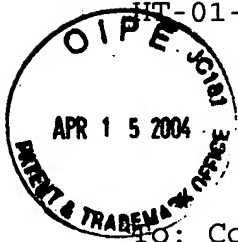


HT-01-012B



April 5, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/791,015 03/02/04

You Feng Zheng et al.

FERROMAGNETIC/ANTIFERROMAGNETIC
BILAYER, INCLUDING DECOUPLER, FOR
LONGITUDINAL BIAS

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on April 12, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 4/12/04

U.S. Patent 5,664,316 to Chen et al., "Method of Manufacturing Magnetoresistive Read Transducer Having a Contiguous Longitudinal Bias Layer," discloses that a ferromagnetic/antiferromagnetic coupled layer could be used to replace a permanent magnet.

U.S. Patent 5,528,440 to Fontana et al., "Spin Valve Magnetoresistive Element with Longitudinal Exchange Biasing of End Regions Abutting the Free Layer, and Magnetic Recording System Using the Element," discloses an improved spin valve (SV) magnetoresistive element having its free ferromagnetic layer in the form of a central active region with defined edges and end regions that are contiguous with and abut the edges of the central active region.

U.S. Patent 6,185,078 to Lin et al., "Spin Valve Read Head with Antiferromagnetic Oxide Film as Longitudinal Bias Layer and Portion of First Read Gap," discloses using a layer of nickel oxide as a pinning layer for a NiFe bias layer.

U.S. Patent 5,705,973 to Yuan et al., "Bias-Free Symmetric Dual Spin Valve Giant Magnetoresistance Transducer," discloses a structure eliminating the bias point offset present in prior dual spin vlave sensors.

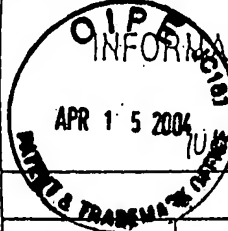
HT-01-012B

U.S. Patent 5,856,897 to Mauri, "Self-Biased Dual Spin Valve Sensor," discloses a stabilization layer under the lead layer.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761



INFORMATION DISCLOSURE CITATION IN AN APPLICATION

APR 15 2004

(Use several sheets if necessary)

Document Number (Optional)

HT-01-012B

Application Number

10/791,015

Applicant

You Feng Zheng et al.

Filing Date

03/02/04

Drawn At Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	NUMO DATE & APPROXIMATE
	5528440	6/18/96	Fontana et al.	360	113	7/26/94
	6185078	2/6/01	Lin et al.	360	324.12	8/21/98
	5705973	1/6/98	Yuan et al.	338	32R	8/26/96
	5856897	1/5/99	Mauri	360	113	11/26/97
	5664316	9/9/97	Chen et al.	29	603.08	5/10/95

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Port/norx Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.